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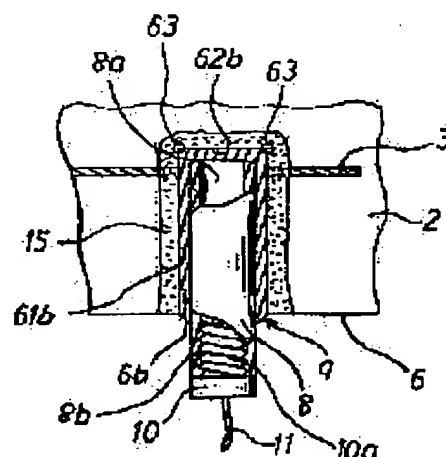
(72)Inventor : NAGASAKI KOICHI

(54) POWER FEEDING STRUCTURE FOR WAFER HOLDER

(57)Abstract:

PROBLEM TO BE SOLVED: To protect a ceramic board against damage when a feeding terminal is fixed by brazing by a method wherein a fixing hole is bored penetrating through a heater electrode, a metallized layer is formed on the inner wall of the fixing hole, and the feeding terminal is joined to the side wall or base of the fixing hole by brazing.

SOLUTION: A fixing hole 6b for mounting a feeding terminal 8 is bored in the rear 6 of a ceramic board penetrating through a heater electrode, and a metallized layer 15 is formed on the side wall 61b and base 62b of the fixing hole 6b which includes a suction electrode 3. Brazing material 9 is applied onto the side wall 61b of the fixing hole 6b, and the feeding terminal 8 is inserted into the fixing hole 6b and fixed by heating carried out at a prescribed temperature. As mentioned above, the hollow feeding terminal 8 is fixed to only the side wall 61b by brazing without being brazed to the base 62b so as to be lessened in brazing area, whereby stress induced in the feeding terminal 8 in the direction vertical to the axial direction of the terminal 8 is relaxed, so that stress is restrained from concentrating on a corner 63.



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POWER FEEDING STRUCTURE FOR WAFER HOLDER

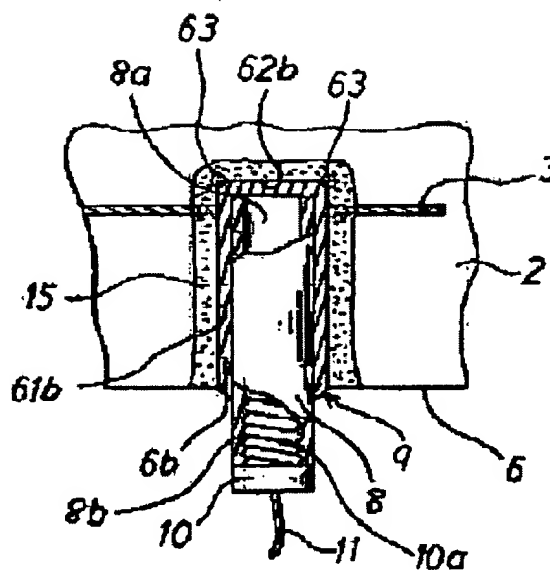
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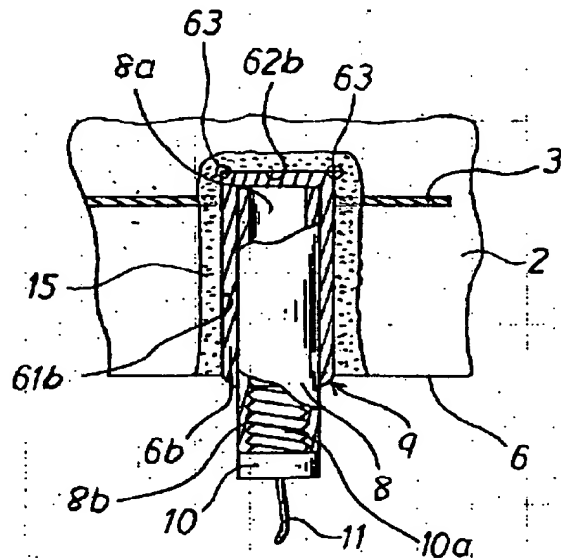
(71) 出願人 000006633
京セラ株式会社
京都府京都市山科区東野北井ノ上町 5 番地
の22
(72) 発明者 長崎 浩一
鹿児島県国分市山下町 1 番 1 号 京セラ株
式会社鹿児島国分工場内

(54) 【発明の名称】 ウエハ保持装置の給電構造

(57) 【要約】

【課題】 静電チャックやサセブタなどのセラミックスからなるウエハ保持装置内に内蔵する吸着用電極、ヒータ電極、高周波発生用電極への給電端子のロウ付け固定時や加熱、冷却の繰り返しにおいてウエハ保持装置の破損を防止する。

【解決手段】 セラミック基体の上面を保持面とし、内部に吸着用電極、ヒータ電極、高周波発生用電極などの内部電極を備えてなるウエハ保持装置の給電構造として、上記セラミック基体の裏面に給電端子を取り付けるための固定孔を前記電極を貫通して穿設し、その内壁にメタライズ層を形成するとともに、上記固定孔の内壁の側壁面又は底面のいずれか一方のみにロウ付けをもって給電端子を接合する。



【特許請求の範囲】

【請求項1】セラミック基体の上面を保持面とし、内部に少なくとも一つの電極を備えてなるウエハ保持装置において、上記セラミック基体の裏面に給電端子を取り付けるための固定孔を前記電極を貫通して穿設し、その内壁にメタライズ層を形成するとともに、上記固定孔の内壁の側壁面又は底面のいずれか一方と給電端子をロウ付け固定してなるウエハ保持装置の給電構造。

【請求項2】上記給電端子が中空構造をしたものである請求項1に記載のウエハ保持装置の給電構造。

【請求項3】上記セラミック基体の内部に備える電極が、吸着用電極、ヒータ電極、高周波発生用電極のいずれかである請求項1に記載のウエハ保持装置の給電構造。

【発明の詳細な説明】

【0001】

【発明の属する技術分野】本発明は、半導体ウエハなどのウエハを保持する静電チャックやヒータ内蔵型サセブタなど、セラミック基体の内部に吸着用電極やヒータ電極、あるいは高周波発生用電極を備えるウエハ保持装置の給電構造に関するものである。

【0002】

【従来の技術】従来、半導体装置の製造工程においては、半導体ウエハ（以下、ウエハと略称する）を高精度に保持するために静電チャックやヒータ内蔵型サセブタなどのウエハ保持装置が使用されている。

【0003】例えば、図5に静電チャック51の縦断面図を示すように、セラミック基体52の上面を保持面55とし、内部の上方に吸着用電極53を、下方にヒータ電極54をそれぞれ埋設したものがあった。そして、上記静電チャック51の保持面55にウエハ50を載置し、ウエハ50と吸着用電極53との間に電圧を印加することで、誘電分極によるクーロン力や微小な漏れ電流によるジョンソン・ラーベック力を発現させてウエハ50を保持面55に吸着保持するとともに、ヒータ電極54に通電することによりウエハ50を加熱するようになっていた。

【0004】また、上記セラミック基体52に埋設する吸着用電極53やヒータ電極54などの内部電極への給電構造は、セラミック基体52の裏面56に給電端子57、58を取り付けるための固定孔56a、56bを前記内部電極53、54と連通するように穿設し、該固定孔56a、56bの側壁面にメタライズ層59を形成したあと、外径が3～10mm程度の給電端子57、58を挿入し、固定孔56a、56b及び内部電極53、54とロウ付け固定することにより導通をとるようにしたものがあった。

【0005】

【発明が解決しようとする課題】ところが、前述のような給電構造をもった静電チャック51では次のような課

題があった。

【0006】給電端子57、58をロウ付け固定する場合、900℃程度の高温に加熱しなければならないことから、大きな断面積を有する給電端子57、58をセラミック基体52の固定孔56a、56bにロウ付け固定すると、給電端子57、58とセラミック基体52との間の熱膨張差に起因して接合部分に歪みが残留し、十分な設計、検証がなされていないとセラミック基体52が破損する恐れがあった。

10 【0007】しかも、セラミック基板52に埋設する内部電極53、54は厚みが数μmから数十μmと極めて薄い金属膜であることから、内部電極53、54に直接接合した給電端子57、58に数アンペアから数十アンペアもの電流を印加しながら加熱および冷却を繰り返すと、繰り返し疲労により内部電極53、54の断線を生じるといった課題があった。特に、セラミック基体52を金属との熱膨張差が大きく、かつ他のセラミックスに比べて機械的強度が若干劣る窒化アルミニウムにより形成したものであれば、これらの問題は顕著であった。

20 【0008】また、内部電極53、54への他に給電構造として、内部電極53、54と給電端子57、58とをかしめ圧着したり、給電端子57、58を焼き嵌めにより固定する方法も提案されている（特開平4-104494号公報参照）が、かしめ圧着や焼き嵌めでは、製作上のばらつきが大きく信頼性に欠けるものであった。

30 【0009】その上、静電チャック51を高温に加熱するためにはヒータ電極54に大電流を印加する必要があるため、そのためには断面積の大きな給電端子58を接合しなければならず、接合部分における熱応力が益々増大し、破損の危険が高いものであった。

【0010】

40 【課題を解決するための手段】そこで、本発明は上記課題に鑑み、セラミック基体の上面を保持面とし、内部に吸着用電極、ヒータ電極、高周波発生用電極の少なくとも一つの電極を備えてなるウエハ保持装置の給電構造として、上記セラミック基体の裏面に給電端子を取り付けるための固定孔を前記電極を貫通して穿設し、その内壁にメタライズ層を形成するとともに、上記固定孔の内壁の側壁面又は底面のいずれか一方と給電端子をロウ付け固定したものである。

【0011】

【発明の実施の形態】以下、本発明の実施形態について説明する。

【0012】図1（a）は本発明に係る給電構造を有するウエハ保持装置の一例である静電チャック1を示す斜視図、（b）は（a）のX-X線断面図であり、セラミック基体2の上面を保持面5とするとともに、内部の上方に吸着用電極3を、下方にヒータ電極4をそれぞれ埋設してあり、セラミック基体2の裏面6には上記吸着用電極3及びヒータ電極4にそれぞれ通電するための給電

端子7、8を固定してある。

【0013】そして、上記静電チャック1の保持面5に半導体ウエハ50（以下、ウエハと略称する）を載置し、上記吸着用電極3との間に電圧を印加することで誘電分極によるクーロン力や微小な漏れ電流によるジョンソン・ラーベック力を発現させ、ウエハ50を保持面5の平坦精度にならわせて吸着保持させるとともに、ヒータ電極4に電圧を印加することで、ウエハ50を均一に加熱するようにしてある。

【0014】このような静電チャック1を構成するセラミック基体2としては、アルミナ、窒化アルミニウム、窒化珪素、炭化珪素、チタン酸バリウム、チタン酸カルシウム、イットリウム-アルミニウム-ガーネット、イットリアなどのセラミックスを採用すれば良い。この中でも特に窒化アルミニウムは、セラミックスの中でも高い熱伝導率を有することから、保持面5に吸着保持したウエハ50を所望の温度に直ちに加熱し、加熱ムラを生じることなく均一に加熱することができるとともに、成膜工程やエッチング工程で使用されているハロゲン系腐食性ガスに対して優れた耐蝕性を有することから、静電チャック1を構成するのに好適である。

【0015】なお、上記静電チャック1の保持面5は、ウエハ50を歪ませることなく吸着保持するために平坦度が10 μ m以下の極めて平坦な面に仕上げてある。

【0016】ところで、セラミック基体2に埋設する吸着用電極3やヒータ電極4などの内部電極への給電構造としては、セラミック基体2の裏面6に給電端子7、8を取り付けるための固定孔6a、6bを前記内部電極3、4を貫通して穿設するとともに、給電端子7、8を固定孔6a、6bの内壁の側壁面又は底面のいずれか一方とロウ付け固定すれば良い。

【0017】以下、内部電極3、4への給電構造の詳細について、ヒータ電極4への給電構造を例にとって説明する。

【0018】図2は、図1のA部を示す拡大図であり、セラミック基体2の裏面6に給電端子8を取り付けるための固定孔6bをヒータ電極4を貫通して穿設するとともに、上記吸着用電極3を含む固定孔6bの側壁面61b及び底面62bにメタライズ層15を形成してある。なお、メタライズ層15の層厚みとしては数十 μ m程度あれば良い。

【0019】そして、上記固定孔6bの側壁面61bにロウ材9を塗布しつつ給電端子8を挿入し、所定の高温雰囲気中で加熱することでロウ付け固定するのであるが、上記給電端子8は内部に内孔8aを持った中空構造の給電端子8を固定したものである。

【0020】即ち、給電端子8をロウ付け固定するには900℃程度の高温で加熱する必要があることから、内孔を有していない中実構造の給電端子8を用いると給電端子8の軸方向ならびに軸に対して垂直な方向における

セラミック基体2との間の熱膨張差が大きすぎるために、固定孔6bのコーナー部63に応力が集中してクラックが発生するのであるが、本発明は、中空構造の給電端子8を用いて固定孔6bの側壁面61bとのみロウ付け固定し、底面62bとのロウ付け面積を減らしてあることから、給電端子8の軸方向と垂直な方向の応力を緩和して固定孔6bのコーナー部63における応力集中を抑制するとともに、固定孔6bの側壁面61bにはメタライズ層15を形成してロウ材9が分散し易くしてあるため、熱膨張差に伴う応力を吸収してセラミック基体2の破損を防止することができる。

【0021】しかも、給電端子8を固定する固定孔6bは薄肉のヒータ電極4を貫通して穿設し、かつ上記ヒータ電極4を含む固定孔6bの側壁面61bにメタライズ層15を形成してヒータ電極4と導通がとれるようにしてあることから、静電チャック1を高温に加熱するために大きな電圧を印加してもヒータ電極4の断線を生じることなく確実に通電することができる。

【0022】このように、本発明によれば、固定孔6bをヒータ電極4を貫通して形成し、その側壁面61b及び底面62bにメタライズ層15を形成するとともに、中空構造の給電端子8をロウ付け固定して、固定孔6bの側壁面61bとのみロウ付け固定する構造としてあることから、ロウ付け固定時における加熱においてセラミック基体2を破損することがなく、また、ヒータ電極4への通電による加熱、冷却の繰り返しにおいてもヒータ電極4の断線及びセラミック基体2の破損を生じることがない。

【0023】ところで、中空構造の給電端子8とは、図3(a)～(c)に示すような、断面形状が円形や楕円形をしたもの、あるいは四角形などの多角形をした内孔8aを有するものなど、少なくとも給電端子8の先端部に内孔8aを有するものであれば良く、必ずしも貫通している必要はない。さらに、図3(d)に示すように、円筒状をした給電端子8にスリット81を設けることでさらに応力を緩和することができる。また、給電端子8の外形状においても円筒状をしたものだけに限らず、楕円や角柱をしたものであっても構わない。

【0024】なお、給電端子8の好ましい寸法としては、内径dに対する最大外径Dの割合が2以下の範囲にあるものが良い。

【0025】これは、内径dに対する外径Dの割合が2より大きくなると、給電端子8の先端部における肉厚が厚くなりすぎるために、固定孔6bのコーナー部63に発生する応力を十分に吸収することができなくなるからである。

【0026】ただし、給電端子8の内径dとは内孔8aの最も短い部分の長さのことであり、外径Dとは外周部において最も長い部分の長さのことである。

【0027】さらに、セラミック基体2の裏面6と給電

端子8との間に逆R状のメニスカスを形成すれば、熱膨張差に起因する応力集中をさらに吸収することができる。

【0028】なお、上記給電端子8とリード線11の接続は、図2に示すように、給電端子8の内孔8aの後端部に雌ネジ部8bを設け、該雌ネジ部8bにリード線11を接続した雄ネジ10aをもった取付金具10を螺合して通電すれば良く、また、リード線11を給電端子8の内孔8aに直接接合しても良い。

【0029】次に、ヒータ電極4への他の給電構造を説明する。

【0030】図4は図2と同様にヒータ電極4への他の給電構造を示す拡大図であり、セラミック基体2の裏面6に給電端子8を取り付けるための固定孔6bをヒータ電極4を貫通して穿設するとともに、上記ヒータ電極4を含む固定孔6bの側壁面61b及び底面62bにメタライズ層15を形成してある。なお、メタライズ層15の層厚みとしては数十 μm 程度あれば良い。

【0031】そして、上記固定孔6bの底面62bにのみロウ材9を塗布して給電端子8をロウ付け固定したものである。

【0032】このように、給電端子8の先端面と固定孔6bの底面62bにのみロウ付け固定すれば、熱膨張差に伴う給電端子8の軸方向の応力が皆無となるために、固定孔6bのコーナー部63における応力集中を抑制し、セラミック基体2の破損を防ぐことができる。

【0033】しかも、給電端子8を固定する固定孔6bは薄肉のヒータ電極4を貫通して穿設するとともに、上記ヒータ電極4を含む固定孔6bの側壁面61b及び底面62bにはメタライズ層15を形成してヒータ電極4と導通がとれるようにしてあることから、静電チャック1を高温に加熱するために大きな電圧を印加してもヒータ電極4の断線を生じることなく確実に通電することができる。

【0034】なお、このような構造とすれば、給電端子8は中空構造だけに限らず図4に示すように中実構造のものであっても構わない。また、上記給電端子8とリード線11の接続は、図4に示すように、給電端子8の雄ネジ8cと、リード線11を接合した円筒状の取付金具10の内孔10bに形成する雌ネジ10cとを螺合して導通をとるようにすれば良い。

【0035】また、図4では、給電端子8の先端面と固定孔6bの底面62bにのみロウ付け固定した例を示したが、逆に、給電端子8の外周面と固定孔6bの側壁面61bにのみロウ付け固定しても良く、この場合、熱膨張差に伴う給電端子8の軸方向に対して垂直な方向の応力が皆無となるために、図4に示す給電構造と同様に固定孔6bのコーナー部63における応力集中を抑制してセラミック基体2の破損を防ぐことができる。

【0036】これら図2及び図4に示す給電構造のよう

に、固定孔6bをヒータ電極4を貫通して穿設し、その側壁面61b及び底面62bにメタライズ層15を形成したあと、上記側壁面61b又は底面62bのいずれか一方のみに給電端子8をロウ付け固定する構造とすれば、接合時及び使用時においてセラミック基体2の破損及びヒータ電極4の断線を生じることがない。

【0037】ただし、固定孔6bに形成するメタライズ層15は少なくとも側壁面61bに形成してあれば良く、底面62bに給電端子8をロウ付けする場合には、底面62bにもメタライズ層15を形成すれば良い。

【0038】なお、本発明に係る給電構造において、ヒータ電極4に通電するための給電端子8の材質としては、高い耐熱性を有するとともに、セラミック基体2の熱膨張係数に近似したものが良く、例えば、タングステン、モリブデン、タンタル、コバルトなどの金属により形成すれば良い。これらの金属は500℃程度の高温下でも使用可能であるとともに、熱膨張係数が $3 \times 10^{-6} \sim 7 \times 10^{-6} / ^\circ\text{C}$ とセラミック基体2の熱膨張係数($3 \times 10^{-6} \sim 7.8 \times 10^{-6} / ^\circ\text{C}$)と近似していることから、セラミック基体2に加わる応力を軽減することができる。

【0039】また、図2又は図4においてはヒータ電極4への給電構造を例にとって説明したが、図1の静電チャック1における吸着用電極3への給電構造も同様の構造としてあり、給電端子7の接合時は勿論のこと、大きく吸着力を得るために吸着用電極3に大きな電圧を印加してもセラミック基体2の破損及び吸着用電極3の断線を生じることがない。

【0040】さらに、図1にはセラミック基体2の内部に吸着用電極3とヒータ電極4を埋設した例を示したが、さらに、高周波発生用電極を埋設しても良く、この電極への給電構造も図2に示すヒータ電極4と同様の給電構造を用いれば良い。

【0041】以上のように、図1では静電チャック1を例にとって説明したが、本発明はヒータ電極や高周波発生用電極を内蔵したサセプタなど、セラミック基体2の内部に電極を内蔵するウエハ保持装置にも適用できることは言うまでもない。

【0042】

【実施例】

(実施例1) ここで、図2及び図4に示す本発明の給電構造を用いた図1の静電チャック1と、従来の給電構造を用いた図5の静電チャック51を試作し、給電端子7、8、57、58の接合実験を行った。

【0043】本実験で使用する静電チャック1、51は、まず、平均粒子径が1.2 μm 程度である純度99.9%のAlN粉末にバインダーと溶媒のみを添加混合して泥漿を製作し、ドクターブレード法により厚さ0.4mm程度のグリーンシートを複数枚成形した。このうち2枚のグリーンシートにAlN粉末を混ぜたタン

グステン(W)のペーストをスクリーン印刷機でもって敷設して吸着用電極3, 53をなす金属ペースト膜とヒータ電極4, 54をなす金属ペースト膜をそれぞれに形成した。そして、各金属ペースト膜を敷設したグリーンシートと残りのグリーンシートを積層して80°C、50kg/cm²の圧力で熱圧着してグリーンシート積層体を形成したあと切削加工を施して円板状とし、該円板状のグリーンシート積層体を真空脱脂し、しかるのち、真空雰囲気にて2000°C程度の温度で5時間焼成して、外径200mm、肉厚10mmで、かつ内部に膜厚15μm程度の吸着用電極3, 53とヒータ電極4, 54をそれぞれ備えるセラミック基体2, 52を形成し、吸着用電極3, 53が埋設されている側のセラミック基体2, 52の表面に研磨加工を施して保持面5を形成することにより製作した。

【0044】そして、本発明のものとして、静電チャック1の裏面6に前記吸着用電極3及びヒータ電極4を貫通する固定孔6a, 6bをそれぞれ穿設し、この側壁面61b及び底面62bにメタライズ層15を形成したあと、図2及び図4の給電構造を用いてモリブデンからなる給電端子7, 8をロウ付け固定し、比較例として、静電チャック51の裏面56に給電端子57, 58を取り付けるための固定孔56a, 56bを前記内部電極53, 54を貫通することなく連通するように穿設し、該固定孔56a, 56bの側壁面にメタライズ層59を形成したあと、モリブデンからなる給電端子7, 8をロウ付け固定した。

【0045】なお、給電端子7, 8の寸法はいずれも外径D10mmの円柱状をしたものを使用し、図2の給電構造に用いる給電端子7, 8には外径D10mm、内径d6mmの円筒状をしたものを使用した。また、メタライズ層15, 59を構成する金属には、銀、銅、チタンの合金を、ロウ材9には銅と銀を重量比で8:2の割合で含有してなる銀銅ロウを使用し、それぞれ900°Cの温度でロウ付け固定した。

【0046】この結果、従来の給電構造を有する静電チャック51では、給電端子58とセラミック基体52との間の熱膨張差に起因する熱応力が大きすぎるためにセラミック基体52にクラックが発生したのに対し、図2及び図4に示す本発明の給電構造を有する静電チャック1においてはセラミック基体2の破損は見られなかった。

【0047】(実施例2)次に、図1に示す静電チャック1のヒータ電極4に、図2に示す給電構造を用いて外径D/内径d比が異なる円筒状の給電端子8をロウ付け固定し、該給電端子8に2kWの電力を印加して、100°C/分の急加熱を行う実験を行った。

【0048】それぞれの結果は表1に示す通りである。

【0049】

【表1】

給電端子 の形状	外径D (mm)	内径d (mm)	外径/内径	クラック の有無
円筒体	7	5	1.4	無し
	7	2	2.3	有り
	10	4	2.5	有り
	10	5	2.0	無し
	10	6	1.6	無し
	20	8	2.5	有り
	20	10	2.0	無し
	20	12	1.6	無し

【0050】この結果、外径D/内径d比が2より大きくなると円筒状の給電端子8を使用したとしても給電端子8とセラミック基体2との間の熱膨張差に起因する応力を緩和する効果が小さく、固定孔6bのコーナー部63を起点とするクラックが発生した。

【0051】これに対し、外径D/内径d比が2より小さい範囲では急加熱を繰り返したとしてもセラミック基体2の破損は見られなかった。

【0052】このことから、中空構造の給電端子8を用いる場合、外径D/内径d比が2より小さい給電端子8を用いれば、加熱、冷却の繰り返しにおいてもセラミック基体2にクラックを生じることなく強固に固定できることが判る。

【0053】

【発明の効果】以上のように、本発明によれば、セラミック基体の上面を保持面とし、内部に吸着用電極、ヒータ電極、高周波発生用電極などの内部電極を備えてなるウエハ保持装置の給電構造として、上記セラミック基体の裏面に給電端子を取り付けるための固定孔を前記電極を貫通して穿設し、その内壁にメタライズ層を形成するとともに、上記固定孔の内壁の側壁面又は底面のいずれか一方のみにロウ付けでもって給電端子を接合したことから、給電端子のロウ付け固定時におけるセラミック基体の破損を防ぐことができるのと同時に、ロウ付け固定後の内部応力を緩和することができるため、熱サイクルに伴う急加熱の繰り返しにおいてもセラミック基体を破損

させたり、内部電極の断線を生じることなく、強固に固定することができ、各電極に確実に通電することができる。

【図面の簡単な説明】

【図1】(a)は本発明に係る給電構造を有するウエハ保持装置の一例である静電チャック1を示す斜視図であり、(b)は(a)のX-X線断面図である。

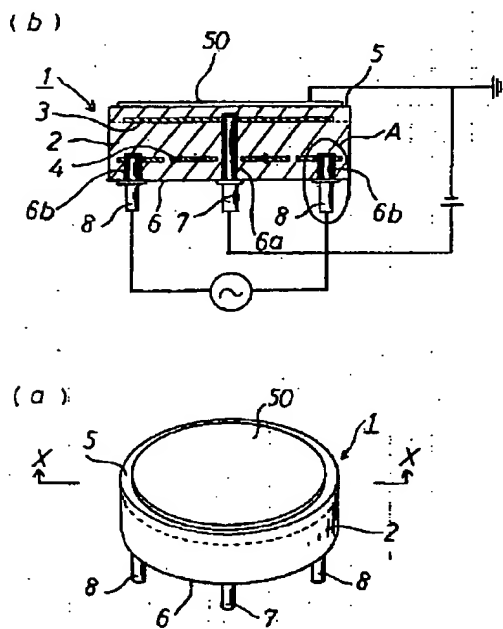
【図2】図1のA部を示す拡大図である。

【図3】(a)～(c)は本発明に係る給電構造に用いるさまざまな形状を有する給電端子を示す斜視図である。

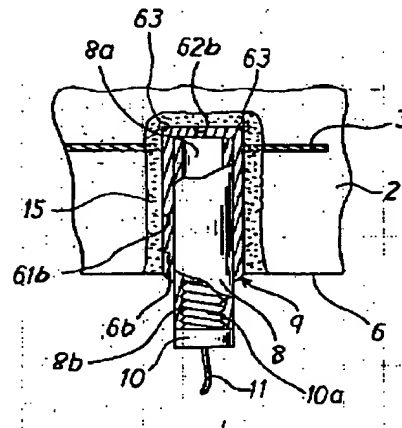
10

* 15…メタライズ層 50…半導体ウエハ

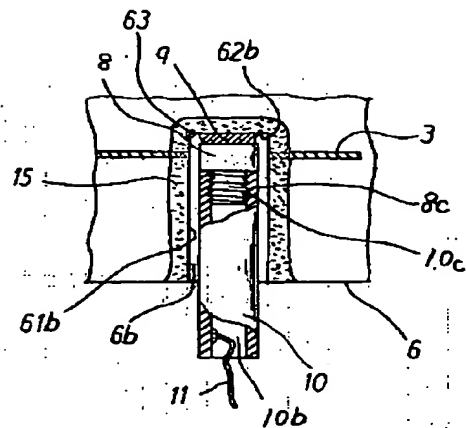
【図1】



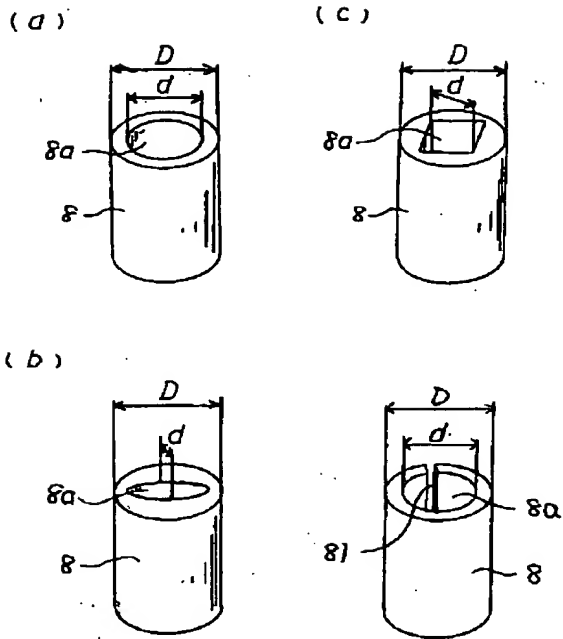
【図2】



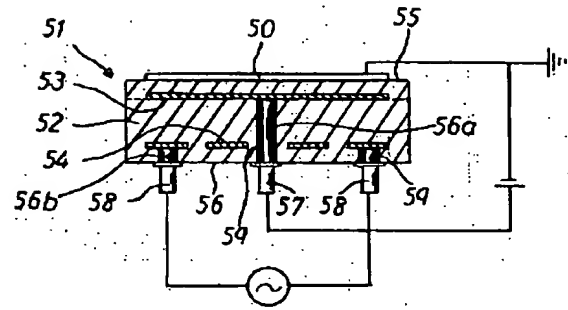
【図4】



【図3】



【図5】



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CLAIMS

[Claim(s)]

[Claim 1] Electric-supply structure of the wafer supporting structure which makes the top face of a ceramic base a maintenance side, and comes to carry out low attachment immobilization of either and the electric-supply terminal of the side-attachment-wall side of the wall of the above-mentioned fixed hole, or a base while penetrating said electrode at the rear face of the above-mentioned ceramic base, drilling the fixed hole for attaching an electric-supply terminal in it in the wafer supporting structure which comes to prepare at least one electrode for the interior and forming a metallized layer in the wall.

[Claim 2] Electric supply structure of the wafer supporting structure according to claim 1 where the above-mentioned electric supply terminal has hollow structure.

[Claim 3] Electric supply structure of the wafer supporting structure according to claim 1 where the electrode with which the interior of the above-mentioned ceramic base is equipped is the electrode for adsorption, a heater electrode, or an electrode for RF generating.

[Translation done.]

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DETAILED DESCRIPTION

[Detailed Description of the Invention]

[0001]

[Field of the Invention] This invention relates to the electric supply structure of the wafer supporting structure which equips the interior of ceramic bases, such as an electrostatic chuck, a heater built-in susceptor, etc. holding wafers, such as a semi-conductor wafer, with the electrode for adsorption, a heater electrode, or the electrode for RF generating.

[0002]

[Description of the Prior Art] Conventionally, in the production process of a semiconductor device, in order to hold a semi-conductor wafer (it is hereafter called a wafer for short) with high precision, the wafer supporting structure, such as an electrostatic chuck and a heater built-in susceptor, is used.

[0003] For example, as drawing of longitudinal section of the electrostatic chuck 51 was shown in drawing 5, the top face of the ceramic base 52 was made into the maintenance side 55, and there were some which laid the heater electrode 54 underground for the electrode 53 for adsorption caudad above the interior, respectively. And a wafer 50 is laid in the maintenance side 55 of the above-mentioned electrostatic chuck 51, and while making the Coulomb force by dielectric polarization, and the Johnson Ra Bec force by the minute leakage current discover and carrying out adsorption maintenance of the wafer 50 in the maintenance side 55 by impressing an electrical potential difference between a wafer 50 and the electrode 53 for adsorption, a wafer 50 is heated by energizing to the heater electrode 54.

[0004] Moreover, the electric supply structure to internal electrodes laid under the above-mentioned ceramic base 52, such as the electrode 53 for adsorption, and the heater electrode 54 after puncturing so that the fixed holes 56a and 56b for attaching the electric supply terminals 57 and 58 in the rear face 56 of the ceramic base 52 may be opened for free passage with said internal electrodes 53 and 54, and forming a metallized layer 59 in the side-attachment-wall side of these fixed holes 56a and 56b. The electric supply terminals 57 and 58 whose outer diameters are about 3-10mm were inserted, and there were some which took the flow by carrying out low attachment immobilization with the fixed holes 56a and 56b and internal electrodes 53 and 54.

[0005]

[Problem(s) to be Solved by the Invention] However, the following technical problems occurred by the electrostatic chuck 51 with the above electric supply structures.

[0006] If low attachment immobilization of the electric supply terminals 57 and 58 which have the big cross section from it having to heat to an about 900-degree C elevated temperature is carried out at the fixed holes 56a and 56b of the ceramic base 52 when carrying out low attachment immobilization of the electric supply terminals 57 and 58 It originated in the differential thermal expansion between the electric supply terminals 57 and 58 and the ceramic base 52, and distortion remained to a part for a joint, and when sufficient design and verification were not made, there was a possibility that the ceramic base 52 might be damaged.

[0007] And the internal electrodes 53 and 54 laid under the ceramic substrate 52 had the technical problem that an open circuit of internal electrodes 53 and 54 was produced by repeat

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2, such as the electrode 3 for adsorption, and the heater electrode 4 What is necessary is just to carry out low attachment immobilization of the electric supply terminals 7 and 8 with either the side-attachment-wall side of the wall of the fixed holes 6a and 6b, or a base, while penetrating said internal electrodes 3 and 4 at the rear face 6 of the ceramic base 2 and drilling the fixed holes 6a and 6b for attaching the electric supply terminals 7 and 8 in it.

[0017] Hereafter, the detail of the electric supply structure to internal electrodes 3 and 4 is explained taking the case of the electric supply structure to the heater electrode 4.

[0018] Drawing 2 is the enlarged drawing showing the A section of drawing 1, and it has formed the metallized layer 15 in side-attachment-wall side 61b and base 62b containing the above-mentioned electrode 3 for adsorption of fixed hole 6b while it penetrates the heater electrode 4 and drills fixed hole 6b for attaching the electric supply terminal 8 in the rear face 6 of the ceramic base 2. In addition, there should just be about dozens of micrometers as a bed depth of a metallized layer 15.

[0019] And although low attachment immobilization is carried out by inserting the electric supply terminal 8 and heating in a predetermined elevated-temperature ambient atmosphere, applying the low material 9 to side-attachment-wall side 61of above-mentioned fixed hole 6b b, the above-mentioned electric supply terminal 8 fixes the electric supply terminal 8 of the hollow structure which had inner hole 8a in the interior.

[0020] namely, from it being necessary to heat the electric supply terminal 8 at an about 900-degree C elevated temperature to carry out low attachment immobilization Although stress will concentrate on the corner section 63 of fixed hole 6b and a crack will occur to the shaft orientations and the shaft of the electric supply terminal 8 since the differential thermal expansion between the ceramic bases 2 in a perpendicular direction is too large if the electric supply terminal 8 of the solid structure where it does not have the inner hole is used This invention carries out low attachment immobilization using the electric supply terminal 8 of hollow structure only with side-attachment-wall side 61of fixed hole 6b b. Since a low attachment area with base 62b is reduced, while easing the stress of a direction perpendicular to the shaft orientations of the electric supply terminal 8 and controlling the stress concentration in the corner section 63 of fixed hole 6b A metallized layer 15 is formed in side-attachment-wall side 61of fixed hole 6b b, since the low material 9 is made easy to distribute, the stress accompanying a differential thermal expansion can be absorbed and breakage of the ceramic base 2 can be prevented.

[0021] And since fixed hole 6b which fixes the electric supply terminal 8 forms a metallized layer 15 in side-attachment-wall side 61of fixed hole 6b which penetrates and drills heater electrode 4 of thin meat, and contains above-mentioned heater electrode 4 b and enables it to have taken the heater electrode 4 and the flow, it can be energized certainly, without producing an open circuit of the heater electrode 4, even if it impresses a big electrical potential difference, in order to heat the electrostatic chuck 1 to an elevated temperature.

[0022] Thus, while according to this invention penetrating the heater electrode 4, forming fixed hole 6b and forming a metallized layer 15 in the side-attachment-wall side 61b and base 62b From having considered as the structure which carries out low attachment immobilization only with side-attachment-wall side 61of fixed hole 6b b The ceramic base 2 is not damaged in heating at the time of low attachment immobilization, and an open circuit of the heater electrode 4 and breakage of the ceramic base 2 are not produced in the repeat of heating by the energization to the heater electrode 4, and cooling.

[0023] By the way, it does not necessarily need to penetrate that what is necessary is just things which have inner hole 8a in the point of the electric supply terminal 8 at least, such as what has inner hole 8a which carried out the polygon of the thing to which the cross-section configuration as shown in drawing 3 RD 3 (a) - (c) carried out the round shape and the ellipse form, or a square, in the electric supply terminal 8 of hollow structure. Furthermore, as shown in drawing 3 (d), stress can be further eased by forming a slit 81 in the electric supply terminal 8 which carried out the shape of a cylinder. Moreover, it does not matter even if it carries out the thing, ellipse, and prism which carried out the shape of a cylinder also in the shape of an

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fatigue, when heating and cooling were repeated impressing a several A to dozens of A current to the electric supply terminals 57 and 58 directly joined to internal electrodes 53 and 54, since thickness was several micrometers to dozens of micrometers, and a very thin metal membrane. In especially the thing in which the differential thermal expansion with a metal formed the ceramic base 52 by the aluminium nitride which is inferior in a mechanical strength a little greatly compared with other ceramics, these problems were remarkable.

[0008] moreover — carrying out caulking sticking by pressure of the internal electrodes 53 and 54 and the electric supply terminals 57 and 58 other than internal electrodes 53 and 54 as electric supply structure *** — the electric supply terminals 57 and 58 — burning — inserting in — the approach of fixing is also proposed — *** (refer to JP.4-104494A) — caulking sticking by pressure — burning — inserting in — coming out — dispersion on manufacture was what lacks in dependability greatly.

[0009] In order to heat the electrostatic chuck 51 to an elevated temperature moreover, the high current needed to be impressed to the heater electrode 54, for that purpose, the big electric supply terminal 58 of the cross section had to be joined, the thermal stress in a part for a joint increased increasingly, and the risk of breakage was high.

[0010]

[Means for Solving the Problem] then, as electric supply structure of the wafer supporting structure which this invention makes the top face of a ceramic base a maintenance side in view of the above-mentioned technical problem, and comes to prepare at least one electrode of the electrode for adsorption, a heater electrode, and the electrode for RF generating for the interior While penetrating said electrode at the rear face of the above-mentioned ceramic base, drilling the fixed hole for attaching an electric supply terminal in it and forming a metallized layer in the wall, low attachment immobilization of either and the electric supply terminal of the side-attachment-wall side of the wall of the above-mentioned fixed hole or a base is carried out.

[0011]

[Embodiment of the Invention] Hereafter, the operation gestalt of this invention is explained.

[0012] While the perspective view showing the electrostatic chuck 1 which is an example of the wafer supporting structure which has the electric supply structure concerning this invention, and (b) are X-ray sectional views of (a) and drawing 1 (a) makes the top face of the ceramic base 2 the maintenance side 5 The heater electrode 4 is caudad laid underground for the electrode 3 for adsorption above the interior, respectively, and the electric supply terminals 7 and 8 for energizing, respectively to the above-mentioned electrode 3 for adsorption and the heater electrode 4 are fixed to the rear face 6 of the ceramic base 2.

[0013] To the maintenance side 5 of the above-mentioned electrostatic chuck 1, and the semi-conductor wafer 50 Lay (it is hereafter called a wafer for short), and the Coulomb force by dielectric polarization and the Johnson Ra Bec force by the minute leakage current are made to discover by impressing an electrical potential difference between the above-mentioned electrodes 3 for adsorption. While a wafer 50 is made to learn from the flat precision of the maintenance side 5 and carries out adsorption maintenance, the wafer 50 is heated to homogeneity by impressing an electrical potential difference to the heater electrode 4.

[0014] What is necessary is just to adopt ceramics, such as an alumina, aluminium nitride, silicon nitride, silicon carbide, barium titanate, titanic-acid calcium, an yttrium aluminium garnet, and yttria, as a ceramic base 2 which constitutes such an electrostatic chuck 1. Also in this, since especially aluminium nitride has the corrosion resistance which was excellent to the halogen system corrosive gas currently used at the membrane formation process or the etching process, it is suitable to constitute the electrostatic chuck 1, while it heats immediately the wafer 50 which carried out adsorption maintenance to desired temperature in the maintenance side 5, and it can heat it to homogeneity, without producing heating nonuniformity, since it has thermal conductivity high also in the ceramics.

[0015] In addition, in order that the maintenance side 5 of the above-mentioned electrostatic chuck 1 may carry out adsorption maintenance, without making a wafer 50 distorted, the very flat field 10 micrometers or less is made to display flatness.

[0016] by the way, as electric supply structure to internal electrodes laid under the ceramic base

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appearance of the electric supply terminal 8.

[0024] In addition, what has the rate of the maximum outer diameter D to a bore d in two or less range as a desirable dimension of the electric supply terminal 8 is good.

[0025] This is because the thickness in the point of the electric supply terminal 8 becomes thick too much, so it becomes impossible to fully absorb the stress generated in the corner section 63 of fixed hole 6b if the rate of an outer diameter D to a bore d becomes larger than 2.

[0026] However, the bore d of the electric supply terminal 8 is the die length of the shortest part of inner hole 8a, and an outer diameter D is the die length of the longest part in the periphery section.

[0027] Furthermore, if a reverse R-like meniscus is formed between the rear face 6 of the ceramic base 2, and the electric supply terminal 8, the stress concentration resulting from a differential thermal expansion is further absorbable.

[0028] In addition, lead wire 11 may be directly joined to inner hole 8a of the electric supply terminal 8 that connection of the above-mentioned electric supply terminal 8 and lead wire 11 prepares female screw section 8b in the back end section of inner hole 8a of the electric supply terminal 8, screws the fixing metal 10 with male screw 10a which connected lead wire 11 to this female screw section 8b, and should just energize it as shown in drawing 2.

[0029] Next, other electric supply structures to the heater electrode 4 are explained.

[0030] Drawing 4 is the enlarged drawing showing other electric supply structures to the heater electrode 4 like drawing 2, and it has formed the metallized layer 15 in side-attachment-wall side 61b and base 62b containing the above-mentioned heater electrode 4 of fixed hole 6b while it penetrates the heater electrode 4 and drills fixed hole 6b for attaching the electric supply terminal 8 in the rear face 6 of the ceramic base 2. In addition, there should just be about dozens of micrometers as a bed depth of a metallized layer 15.

[0031] And the low material 9 is applied only to base 62of above-mentioned fixed hole 6b b, and low attachment immobilization of the electric supply terminal 8 is carried out.

[0032] Thus, if low attachment immobilization is carried out only at base 62of apical surface [of the electric supply terminal 8], and fixed hole 6b b, since the stress of the shaft orientations of the electric supply terminal 8 accompanying a differential thermal expansion will become that there is nothing, the stress concentration in the corner section 63 of fixed hole 6b can be controlled, and breakage of the ceramic base 2 can be prevented.

[0033] And while fixed hole 6b which fixes the electric supply terminal 8 penetrates and drills the heater electrode 4 of thin meat From forming a metallized layer 15 in side-attachment-wall side 61of fixed hole 6b b and base 62b containing the above-mentioned heater electrode 4, and enabling it to have taken the heater electrode 4 and the flow It can energize certainly, without producing an open circuit of the heater electrode 4, even if it impresses a big electrical potential difference, in order to heat the electrostatic chuck 1 to an elevated temperature.

[0034] In addition, such structure, then the electric supply terminal 8 may be the things of solid structure, as shown in hollow structure drawing 4. Moreover, what is necessary is for connection of the above-mentioned electric supply terminal 8 and lead wire 11 to screw female screw 10c formed in inner hole 10b of the fixing metal 10 of the shape of a cylinder which joined lead wire 11 to male screw 8c of the electric supply terminal 8, and just to make it take a flow, as shown in drawing 4.

[0035] Moreover, although drawing 4 showed the example which carried out low attachment immobilization only to base 62of apical surface [of the electric supply terminal 8], and fixed hole 6b b On the contrary, since low attachment immobilization may be carried out and the stress of a perpendicular direction becomes that there is nothing in this case only at side-attachment-wall side 61of peripheral face [of the electric supply terminal 8], and fixed hole 6b b to the shaft orientations of the electric supply terminal 8 accompanying a differential thermal expansion The stress concentration in the corner section 63 of fixed hole 6b can be controlled like the electric supply structure shown in drawing 4, and breakage of the ceramic base 2 can be prevented.

[0036] After penetrating the heater electrode 4, drilling fixed hole 6b and forming a metallized layer 15 in the side-attachment-wall side 61b and base 62b like the electric supply structure

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shown in these drawing 2 and drawing 4, breakage of the ceramic base 2 and an open circuit of the heater electrode 4 are not produced at the structure which carries out low attachment immobilization of the electric supply terminal 8, then the time of junction and use in either above-mentioned side-attachment-wall side 61b or base 62b.

[0037] However, that what is necessary is just to have formed in side-attachment-wall side 61b at least, the metallized layer 15 formed in fixed hole 6b should just form a metallized layer 15 also in base 62b, when carrying out low attachment of the electric supply terminal 8 at base 62b.

[0038] In addition, in the electric supply structure concerning this invention, while having high thermal resistance as the quality of the material of the electric supply terminal 8 for energizing to the heater electrode 4, what was approximated to the coefficient of thermal expansion of the ceramic base 2 is good, for example, should just form with metals, such as a tungsten, molybdenum, a tantalum, and covar. Since the coefficient of thermal expansion approximates these metals with $3 \times 10^{-6} \sim 7 \times 10^{-6}/\text{degree C}$ and the coefficient of thermal expansion ($3 \times 10^{-6} \sim 7.8 \times 10^{-6}/\text{degree C}$) of the ceramic base 2 while they are usable also under an about 500-degree C elevated temperature, they can mitigate the stress which joins the ceramic base 2.

[0039] Moreover, although explained taking the case of the electric supply structure to the heater electrode 4 in drawing 2 or drawing 4, in order to also have made electric supply structure to the electrode 3 for adsorption in the electrostatic chuck 1 of drawing 1 into the same structure and to acquire adsorption power greatly not to mention the time of junction of the electric supply terminal 7, even if it impresses a big electrical potential difference to the electrode 3 for adsorption, breakage of the ceramic base 2 and an open circuit of the electrode 3 for adsorption are not produced.

[0040] Furthermore, what is necessary is to lay the electrode for RF generating underground and just to use further, the same electric supply structure as the heater electrode 4 which also shows the electric supply structure to this electrode to drawing 2, although the example which laid the electrode 3 for adsorption and the heater electrode 4 under the interior of the ceramic base 2 was shown in drawing 1.

[0041] As mentioned above, although drawing 1 explained taking the case of the electrostatic chuck 1, it cannot be overemphasized that this invention is applicable also to the wafer supporting structure which builds an electrode in the interior of the ceramic bases 2, such as a susceptor which built in the heater electrode and the electrode for RF generating.

[0042]

[Example]

(Example 1) Here, the electrostatic chuck 1 of drawing 1 using the electric supply structure of this invention shown in drawing 2 and drawing 4 and the electrostatic chuck 51 of drawing 5 using the conventional electric supply structure were made as an experiment, and the junction experiment of the electric supply terminals 7, 8, 57, and 58 was conducted.

[0043] First, the electrostatic chucks 1 and 51 used in this experiment carried out addition mixing only of a binder and the solvent at the AlN powder which is 99.9% of purity whose mean particle diameter is about 1.2 micrometers, manufactured slurry, and fabricated two or more green sheets with a thickness of about 0.4mm with the doctor blade method. Among these, the metal paste film which lays that it is also with a screen printer about the paste of the tungsten (W) which mixed AlN powder with the green sheet of two sheets, and forms the electrodes 3 and 53 for adsorption, and the metal paste film which forms the heater electrodes 4 and 54 were formed in each. The laminating of the green sheet which laid each metal paste film, and the remaining green sheets is carried out. And 80-degreeC, 50kg/cm² After carrying out thermocompression bonding by the pressure and forming a green sheet layered product, perform cutting and it considers as disc-like. Vacuum cleaning of this disc-like green sheet layered product is carried out, and it calcinates at the temperature of about 2000 degrees C in a vacuum ambient atmosphere the appropriate back for 5 hours. With the outer diameter of 200mm, and the thickness of 10mm And it manufactured by forming in the interior the ceramic bases 2 and 52 equipped with the electrodes 3 and 53 for adsorption and the heater electrodes 4 and 54 of about 15 micrometers of thickness, respectively, performing polish processing to the front face

of the near ceramic bases 2 and 52 under which the electrodes 3 and 53 for adsorption are laid, and forming the maintenance side 5 in it.

[0044] And after drilling the fixed holes 6a and 6b which penetrate said electrode 3 for adsorption, and the heater electrode 4 in the rear face 6 of the electrostatic chuck 1 as a thing of this invention, respectively and forming a metallized layer 15 in this side-attachment-wall side 61b and base 62b. Low attachment immobilization of the electric supply terminals 7 and 8 which consist of molybdenum using drawing 2 and the electric supply structure of drawing 4 is carried out. As an example of a comparison it punctures so that the fixed holes 56a and 56b for attaching the electric supply terminals 57 and 58 in the rear face 56 of the electrostatic chuck 51 may be opened for free passage without penetrating said internal electrodes 53 and 54. After forming a metallized layer 59 in the side-attachment-wall side of these fixed holes 56a and 56b, low attachment immobilization of the electric supply terminals 7 and 8 which consist of molybdenum was carried out.

[0045] In addition, each dimension of the electric supply terminals 7 and 8 used what carried out the shape of a cylinder of outer-diameter D10mm, and used what carried out the shape of a cylinder (outer-diameter D10mm and bore d8mm) for the electric supply terminals 7 and 8 used for the electric supply structure of drawing 2. moreover, the silver copper low which 82 comes the alloy of silver, copper, and titanium out of copper and silver comparatively by the weight ratio at the low material 9, and it comes to contain was used for the metal which constitutes metallized layers 15 and 59, and low attachment immobilization was carried out at the temperature of 900 degrees C, respectively.

[0046] Consequently, by the electrostatic chuck 51 which has the conventional electric supply structure, since the thermal stress resulting from the differential thermal expansion between the electric supply terminal 58 and the ceramic base 52 was too large, breakage of the ceramic base 2 was not seen in the electrostatic chuck 1 which has the electric supply structure of this invention shown in the ceramic base 52 to the crack having occurred at drawing 2 and drawing 4.

[0047] (Example 2) Next, low attachment immobilization of the cylinder-like electric supply terminal 8 with which outer-diameter D differs from a bore d ratio using the electric supply structure shown in the heater electrode 4 of the electrostatic chuck 1 shown in drawing 1 at drawing 2 was carried out. 2kW power was impressed to this electric supply terminal 8, and the experiment which performs sudden 100-degree-C heating for /was conducted.

[0048] Each result is as being shown in Table 1.

[0049]
[Table 1]

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電極端子 の形状	外径D (mm)	内径d (mm)	外径/内径	クラック の有無
円筒体	7	5	1.4	無し
	7	2	2.3	有り
	10	4	2.5	有り
	10	5	2.0	無し
	10	6	1.6	無し
	20	8	2.5	有り
	20	10	2.0	無し
	20	12	1.6	無し

[0050] Consequently, when outer-diameter D / bore d ratio became larger than 2, even if it used the cylinder-like electric supply terminal 8, the effectiveness which eases the stress resulting from the differential thermal expansion between the electric supply terminal 8 and the ceramic base 2 was small, and the crack on the basis of the corner section 63 of fixed hole 6b occurred.

[0051] On the other hand, in the range where outer-diameter D / bore d ratio is smaller than 2, even if it repeated sudden heating, breakage of the ceramic base 2 was not seen.

[0052] It turns out that it is firmly fixable, without producing a crack from this in the ceramic base 2 also in the repeat of heating and cooling, if outer-diameter D / bore d ratio uses the electric supply terminal 8 smaller than 2 when using the electric supply terminal 8 of hollow structure.

[0053]

[Effect of the Invention] as mentioned above, according to this invention, as electric supply structure of the wafer supporting structure which makes the top face of a ceramic base a maintenance side, and comes to prepare internal electrodes, such as an electrode for adsorption, a heater electrode, and an electrode for RF generating, for the interior While penetrating said electrode at the rear face of the above-mentioned ceramic base, drilling the fixed hole for attaching an electric supply terminal in it and forming a metallized layer in the wall Since the electric supply terminal was joined as low attachment is also in either the side-attachment-wall side of the wall of the above-mentioned fixed hole, or a base, while being able to prevent breakage of the ceramic base at the time of low attachment immobilization of an electric supply terminal Without damaging a ceramic base or producing an open circuit of an internal electrode also in the repeat of sudden heating accompanying a heat cycle, since the internal stress after low attachment immobilization can be eased, it can fix firmly and can energize certainly to each electrode.

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- 1.This document has been translated by computer. So the translation may not reflect the original precisely.
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DESCRIPTION OF DRAWINGS

[Brief Description of the Drawings]

[Drawing 1] (a) is the perspective view showing the electrostatic chuck 1 which is an example of the wafer supporting structure which has the electric supply structure concerning this invention, and (b) is X-X-ray sectional view of (a).

[Drawing 2] It is the enlarged drawing showing the A section of drawing 1 .

[Drawing 3] (a) - (c) is the perspective view showing the electric supply terminal which has various configurations used for the electric supply structure concerning this invention.

[Drawing 4] It is the enlarged drawing showing other electric supply structures concerning this invention.

[Drawing 5] It is drawing of longitudinal section showing the conventional electrostatic chuck.

[Description of Notations]

1 -- Electrostatic chuck 2 -- Ceramic base 3 -- Electrode for adsorption 4 -- Heater electrode

5 -- Maintenance side 6 -- Rear face 6a, 6b -- Fixed hole 61b -- Side-attachment-wall side
62b -- Base

7 Eight -- Electric supply terminal 9 -- Low material 10 -- Fixing metal 11 -- Lead wire

15 -- Metallized layer 50 -- Semi-conductor wafer

[Translation done.]